

Olivier Latry

List of Publications by Year in descending order

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72
papers

380
citations

1163117

8
h-index

888059

17
g-index

72
all docs

72
docs citations

72
times ranked

343
citing authors

#	ARTICLE	IF	CITATIONS
1	Processing of complex stimuli and natural scenes in the visual cortex. <i>Current Opinion in Neurobiology</i> , 2004, 14, 468-473.	4.2	113
2	Gate oxide degradation of SiC MOSFET under short-circuit aging tests. <i>Microelectronics Reliability</i> , 2016, 64, 415-418.	1.7	24
3	Short-circuit robustness test and in depth microstructural analysis study of SiC MOSFET. <i>Microelectronics Reliability</i> , 2017, 76-77, 527-531.	1.7	18
4	Physical analysis of Schottky contact on power AlGaIn/GaN HEMT after pulsed-RF life test. <i>Microelectronics Reliability</i> , 2012, 52, 2205-2209.	1.7	15
5	A 5000h RF life test on 330 W RF-LDMOS transistors for radars applications. <i>Microelectronics Reliability</i> , 2010, 50, 1574-1576.	1.7	13
6	Compared deep class-AB and class-B ageing on AlGaIn/GaN HEMT in S-Band pulsed-RF operating life. <i>Microelectronics Reliability</i> , 2012, 52, 2561-2567.	1.7	11
7	Reliability Assessment Of AlGaIn/GaN HEMTs on the SiC Substrate Under the RF Stress. <i>IEEE Transactions on Power Electronics</i> , 2021, 36, 7442-7450.	7.9	11
8	Robustness of 4H-SiC 1200V Schottky diodes under high electrostatic discharge like human body model stresses: An in-depth failure analysis. <i>Diamond and Related Materials</i> , 2014, 44, 62-70.	3.9	9
9	Evidence of Mg Segregation to Threading Dislocation in Normally-Off GaN-HEMT. <i>IEEE Nanotechnology Magazine</i> , 2019, 18, 995-998.	2.0	9
10	Ageing of GaN HEMT devices: which degradation indicators?. <i>Journal of Semiconductors</i> , 2016, 37, 014001.	3.7	8
11	Achieving of an optical very high frequency modulated wave source using heterodyne technique. <i>Optics Communications</i> , 2002, 202, 81-90.	2.1	7
12	Characterization of the chirp in semiconductor laser under modulation. <i>Materials Science and Engineering C</i> , 2008, 28, 671-675.	7.3	7
13	Characterization and modeling of hot carrier injection in LDMOS for L-band radar application. <i>Microelectronics Reliability</i> , 2011, 51, 1289-1294.	1.7	7
14	Characterization of HTRB stress effects on SiC MOSFETs using photon emission spectral signatures. <i>Microelectronics Reliability</i> , 2017, 76-77, 243-248.	1.7	7
15	S-band pulsed-RF operating life test on AlGaIn/GaN HEMT devices for radar application. <i>Microelectronics Reliability</i> , 2019, 100-101, 113434.	1.7	7
16	Optimization of the coupling between a tapered fibre and a p-i-n photodiode. <i>Journal Physics D: Applied Physics</i> , 1995, 28, 1562-1572.	2.8	6
17	Performance drifts of N-MOSFETs under pulsed RF life test. <i>Microelectronics Reliability</i> , 2014, 54, 1851-1855.	1.7	6
18	An athermal measurement technique for long time constants traps characterization in GaN HEMT transistors. <i>Microelectronics Reliability</i> , 2015, 55, 1703-1707.	1.7	6

#	ARTICLE	IF	CITATIONS
19	Electrical and Physical Analysis of Thermal Degradations of AlGaIn/GaN HEMT Under Radar-Type Operating Life. IEEE Transactions on Microwave Theory and Techniques, 2016, , 1-11.	4.6	6
20	Extraction of physical Schottky parameters using the Lambert function in Ni/AlGaIn/GaN HEMT devices with defined conduction phenomena. Journal of Semiconductors, 2017, 38, 014007.	3.7	6
21	Modeling of Power GaN HEMT for Switching Circuits Applications Using Levenberg-Marquardt Algorithm. , 2018, , .		6
22	Optical generation of 43 Gbit/s phase-shaped binary transmission format from DPSK signal using 50 GHz periodic optical filter. , 2005, , .		6
23	Localizing and analyzing defects in AlGaIn/GaN HEMT using photon emission spectral signatures. Engineering Failure Analysis, 2017, 81, 69-78.	4.0	5
24	Reliability Study of High-Power Mechatronic Components by Spectral Photoemission Microscopy. , 2017, , 241-271.		5
25	A model for diffusion of beryllium in InGaAs/InP heterostructures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 80, 73-76.	3.5	4
26	Effects of drain quiescent voltage on the ageing of AlGaIn/GaN HEMT devices in pulsed RF mode. Microelectronics Reliability, 2016, 64, 585-588.	1.7	4
27	Optimizing Atom Probe Analysis with Synchronous Laser Pulsing and Voltage Pulsing. Microscopy and Microanalysis, 2017, 23, 221-226.	0.4	4
28	Characterization of ESD stress effects on SiC MOSFETs using photon emission spectral signatures. , 2017, , .		4
29	Failure investigation of packaged SiC-diodes after thermal storage in extreme operating condition. Engineering Failure Analysis, 2018, 83, 185-192.	4.0	4
30	Investigation of the aging of power GaN HEMT under operational switching conditions, impact on the power converters efficiency. Microelectronics Reliability, 2019, 100-101, 113403.	1.7	4
31	Leakage current effects on N-MOSFETs after thermal ageing in pulsed life tests. Microelectronics Journal, 2014, 45, 1800-1805.	2.0	3
32	Thermal Analysis of AlGaIn/GaN High-Electron Mobility Transistors Using 1 μ V Pulsed Characterizations and Infra Red Microscopy. IEEE Transactions on Device and Materials Reliability, 2019, 19, 704-710.	2.0	3
33	Generation of an amplitude modulated optical wave up to 275 GHz by laser wave mixing for optical component bandwidth measurement. Optical Engineering, 2002, 41, 1469.	1.0	2
34	CO ₂ -laser-beam-based technique for producing optical fiber components. , 2003, 5260, 154.		2
35	Fiber-based Mach-Zehnder interferometric structures: principles and required characteristics for efficient modulation format conversion. , 2005, , .		2
36	Simultaneous measures of temperature and expansion on electronic compound. , 2011, , .		2

#	ARTICLE	IF	CITATIONS
37	RF transient pulse signal integrity with ns-duration for atom-probe tomography. , 2015, , .		2
38	RF Pulse Signal Integrity Analysis for Nonlinear Ended Microstrip Line Atom-Probe Tomography. IOP Conference Series: Materials Science and Engineering, 2016, 120, 012006.	0.6	2
39	Temperature estimation of high-electron mobility transistors AlGaIn/GaN. , 2018, , .		2
40	SiC MOSFET robustness to ESD study: Correlation between electrical and spectral photo-emission characterizations. , 2018, , .		2
41	Dopant activity for highly in-situ doped polycrystalline silicon: hall, XRD, scanning capacitance microscopy (SCM) and scanning spreading resistance microscopy (SSRM). Nano Express, 2021, 2, 010037.	2.4	2
42	Reliability Study of Mechatronic Power Components Using Spectral Photon Emission Microscopy. Advanced Electromagnetics, 2016, 5, 20.	1.0	2
43	Parametric investigations and simulations of ion beam etching and reactive ion etching mechanisms for GaAs compounds. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1994, 28, 383-386.	3.5	1
44	<title>Microlens fibers fabricated by a melting-tapering process using a CO$\times 2$ laser</title>. , 1999, , .		1
45	<title>Mixing of two 155-um laser waves in millimeter frequency range for optical components test</title>. , 2002, , .		1
46	Theoretical Study of Semiconductor Laser under Modulation. AIP Conference Proceedings, 2007, , .	0.4	1
47	Experimental considerations on bandwidth measurement of ultra-fast photoreceptors by optical heterodyning. Measurement: Journal of the International Measurement Confederation, 2007, 40, 406-414.	5.0	1
48	New approach for thermal investigation of a III – V power transistor. , 2008, , .		1
49	A workbench development for L-band LDMOS amplifier reliability study (electronic power transistors) Tj ETQq1 1 0.784314 rgBT /Ove		1
50	Channel temperature estimation of AlGaIn/GaN HEMT for pulsed RADAR applications using infrared thermography and electrical characterization. , 2014, , .		1
51	Reliability and Qualification Tests for High-Power MOSFET Transistors. , 2017, , 155-197.		1
52	Estimation of losses of GaN HEMT in power switching applications based on experimental characterization. Computers and Electrical Engineering, 2020, 84, 106622.	4.8	1
53	Enhanced Optical Generation of 42.7 Gbps Phase Shaped Binary Transmission. ETRI Journal, 2006, 28, 826-829.	2.0	1
54	Reliability and failure analysis in power GaN-HEMTs during S-band pulsed-RF operating. Microelectronics Reliability, 2021, 126, 114295.	1.7	1

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55	<title>New pressure optical sensor for distributed sensing</title>. , 1992, 1586, 96.		0
56	<title>Coupling between two optical fibers for stress distributed sensing</title>. , 1993, 2071, 255.		0
57	<title>Modelization of field power distribution in specific singlemode optical fiber for optimal coupling in P-I-N photodiode</title>. , 1994, , .		0
58	<title>Field power distribution in variable core radius of optical fiber for optimal coupling with photodiode</title>. , 1994, , .		0
59	Achieving an amplitude-modulated optical wave up to 275 GHz for optical components test. , 2003, , .		0
60	Tapered step profile index fiber with varying core index along the propagation axis. , 2003, , .		0
61	PDL estimation in a concatenation of all-fiber passive optical components. , 2003, , .		0
62	Optogeometrical variations along the propagation axis in all fiber passive components. , 2003, 5246, 686.		0
63	Two lasers mixing for generation of a modulated optical wave. , 2003, 4829, 367.		0
64	LPFG implementation using electrical-arc and micro-deformations. , 0, , .		0
65	Using MZIs for Optical PSBT Transmissions: Requirements for Thermal Stabilization. ETRI Journal, 2006, 28, 615-620.	2.0	0
66	Comparison of different feedback signals used in one stage PMD compensators for different modulation formats. IEEE Transactions on Communications, 2008, 56, 1722-1728.	7.8	0
67	Adding channels with PSBT format at 40Gbit/s in an existing 10Gbit/s optical network. Optics Communications, 2011, 284, 5125-5129.	2.1	0
68	Physical Defects Analysis of Mechatronic Systems. , 2015, , 49-77.		0
69	High-Efficiency Architecture for Power Amplifiers. , 2015, , 217-241.		0
70	Study of different algorithms and models for trapping effect extraction. , 2016, , .		0
71	Internal Temperature Measurement of Electronic Components. , 2019, , 169-188.		0
72	Aging Power Transistors in Operational Conditions. , 2015, , 23-48.		0